Power Transistors

Panasonic

# 2SA2064

# Silicon PNP epitaxial planar type

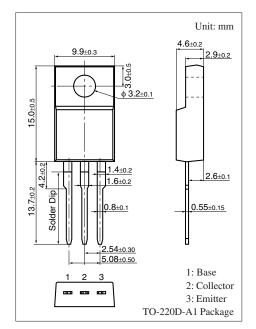
Power supply for audio & visual equipments such as TVs and VCRs Industrial equipments such as DC-DC converters

## Features

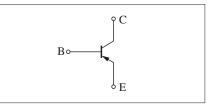
- High speed switching ( $t_{stg}$ : storage time/ $t_f$ : fall time is short)
- $\bullet$  Low collector-emitter saturation voltage  $V_{\mbox{CE(sat)}}$
- $\bullet$  Superior forward current transfer ratio  $h_{F\!E}$  linearity
- TO-220D built-in: Excellent package with withstand voltage 5 kV guaranteed

<b>3</b> <sup>2</sup> C <sup>2</sup> <sup>2</sup>								
Symbol	Rating	Unit						
V <sub>CBO</sub>	-50	V						
V <sub>CEO</sub>	-50	V						
V <sub>EBO</sub>	-6	V						
I <sub>C</sub>	-10	А						
I <sub>CP</sub>	-20	А						
P <sub>C</sub>	25	W						
	2.0							
Tj	150	°C						
T <sub>stg</sub>	-55 to +150	°C						
	V <sub>CBO</sub> V <sub>CEO</sub> V <sub>EBO</sub> I <sub>C</sub> P <sub>C</sub> T <sub>j</sub>	$\begin{array}{c c c c c c c c } \hline V_{CBO} & -50 \\ \hline V_{CEO} & -50 \\ \hline V_{CEO} & -50 \\ \hline V_{EBO} & -6 \\ \hline I_C & -10 \\ \hline I_C & -10 \\ \hline I_C & -20 \\ \hline P_C & 25 \\ \hline 2.0 \\ \hline T_j & 150 \\ \hline \end{array}$						

# Absolute Maximum Ratings $T_C = 25^{\circ}C$



#### Internal Connection

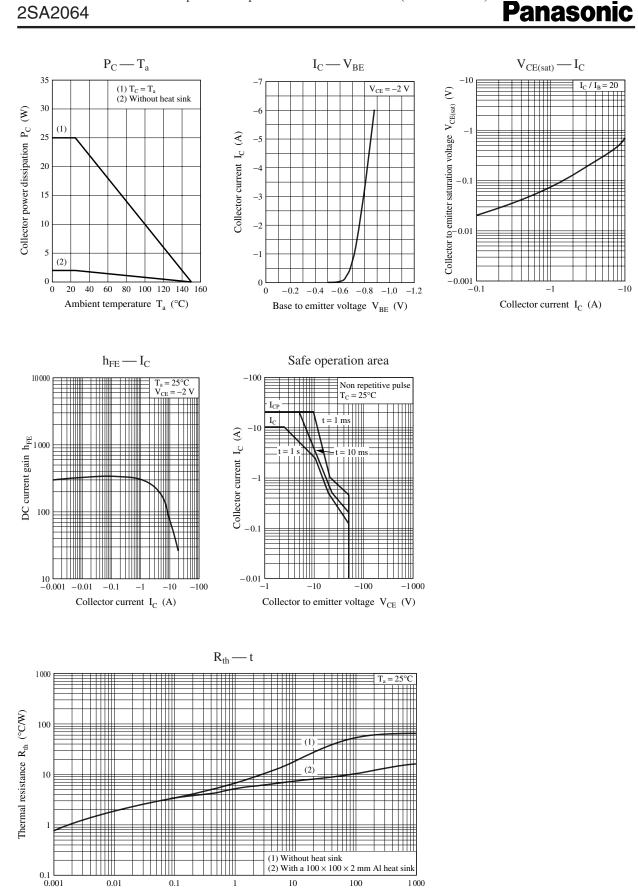


# Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$			-100	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_B = 0$			-100	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = -2 V, I_C = -1 A$	200			—
	h <sub>FE2</sub>	$V_{CE} = -2 V, I_C = -7 A$	100			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -5 \text{ A}, I_{\rm B} = -250 \text{ mA}$			- 0.5	V
Turn-on time	t <sub>on</sub>	$I_{\rm C} = -4$ A, Resistance loaded			0.5	μs
Storage time	t <sub>stg</sub>	$I_{B1} = -0.4 \text{ A}, I_{B2} = 0.4 \text{ A}$			1.0	μs
Fall time	t <sub>f</sub>	$V_{CC} = -40 \text{ V}$			0.15	μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

# 2SA2064



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Time t (s)

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